/ Descriptions

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

/ Features

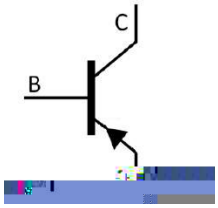
600mA

Collector currents to 600mA.HF Product.

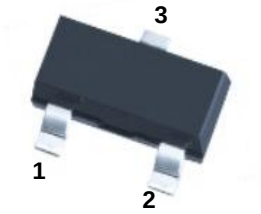
/ Applications

General purpose amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

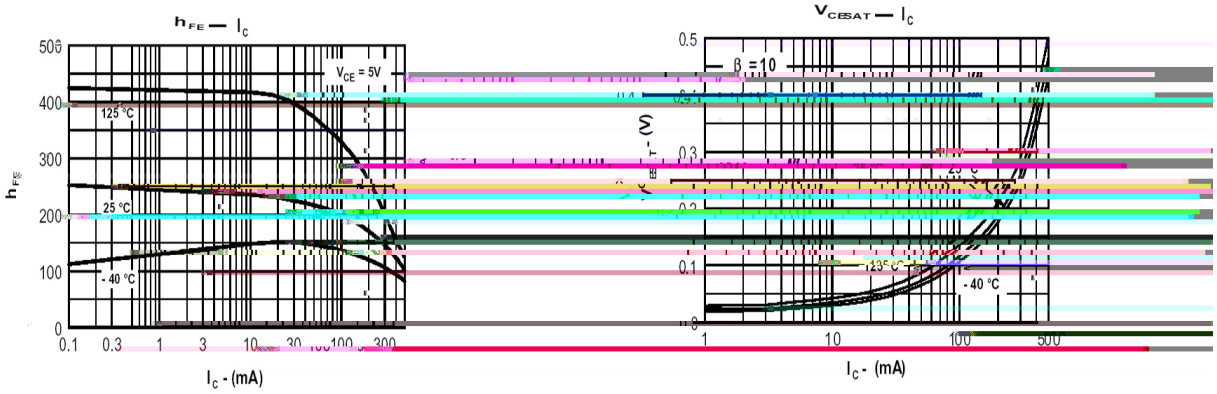
/ h_{FE} Classifications & Marking

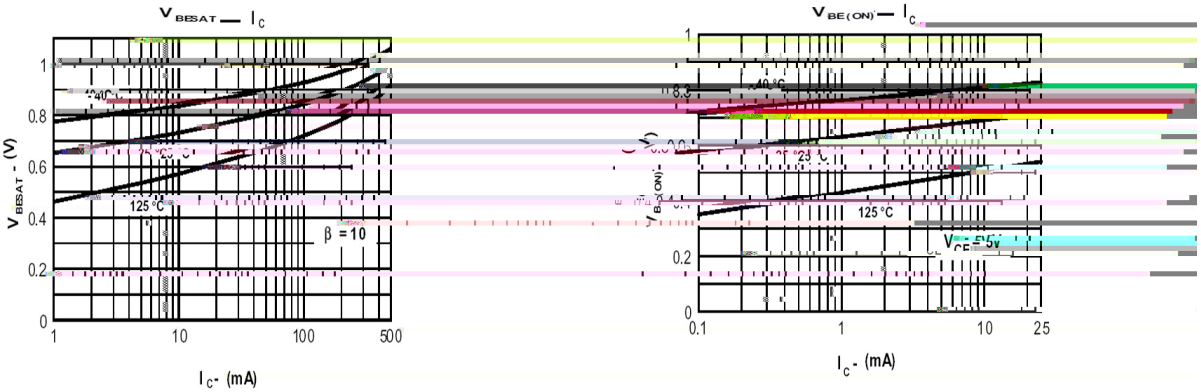
h_{FE} Range	100 300
Marking	G2F

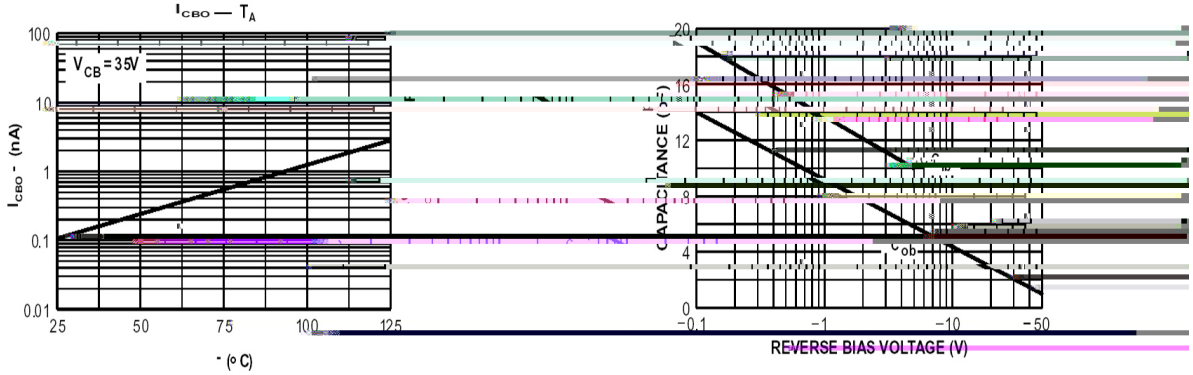
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-600	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-10μA I_E=0	-60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-10mA I_B=0	-60			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-10μA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-50V I_E=0			-0.01	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-10V I_C=-150mA*	100		300	
	$h_{FE(2)}$	V_{CE}=-10V I_C=-500mA*	50			
	$h_{FE(3)}$	V_{CE}=-10V I_C=-10mA	100			
	$h_{FE(4)}$	V_{CE}=-10V I_C=-1.0mA	100			
	$h_{FE(5)}$	V_{CE}=-10V I_C=-0.1mA	75			
Collector-Emitter Saturation Voltage	$V_{CE(sat)\ (1)}$	I_C=-150mA I_B=-15mA			-0.4	V
	$V_{CE(sat)\ (2)}$	I_C=-500mA I_B=-50mA			-1.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)\ (1)}$					

/ Electrical Characteristic Curve



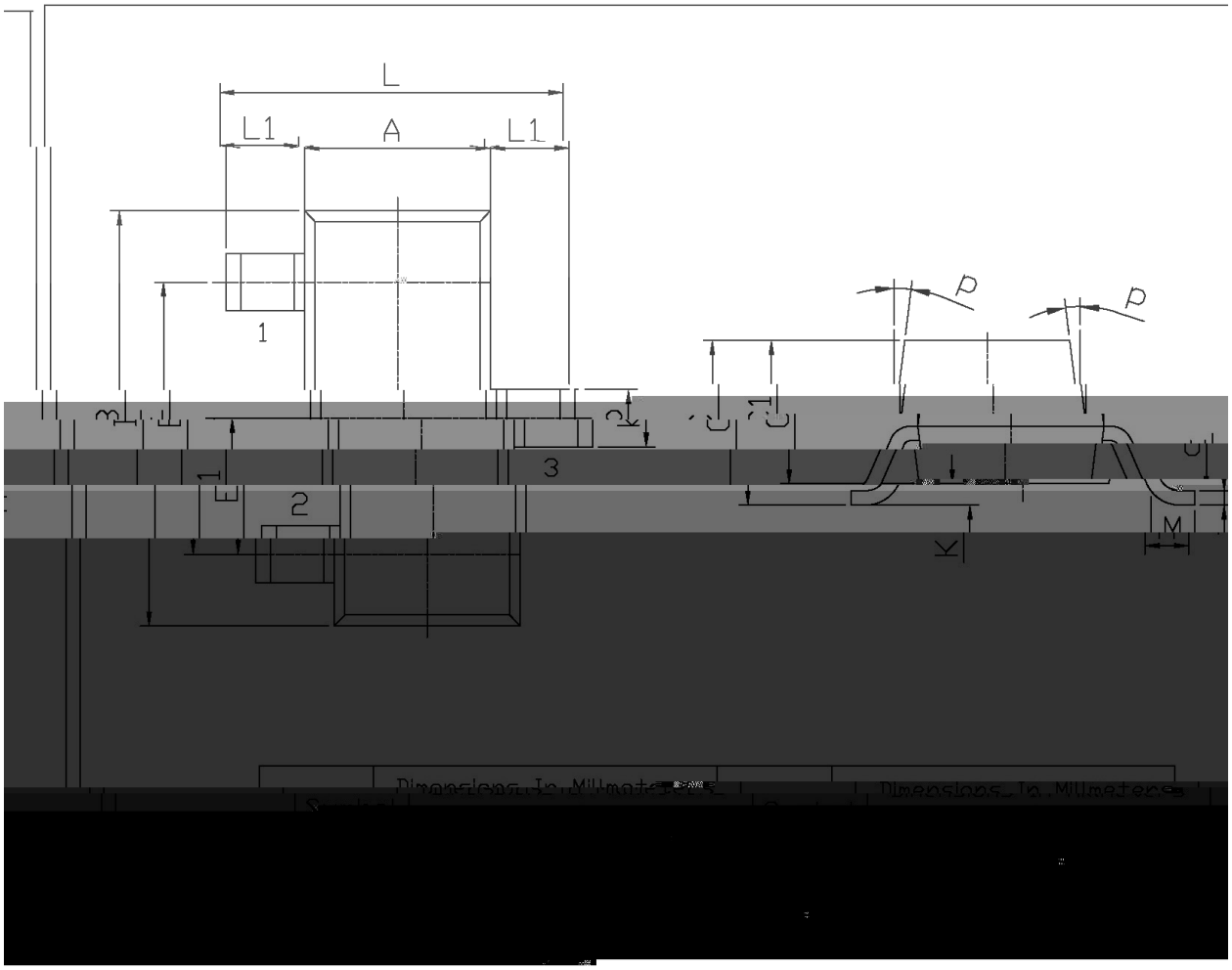




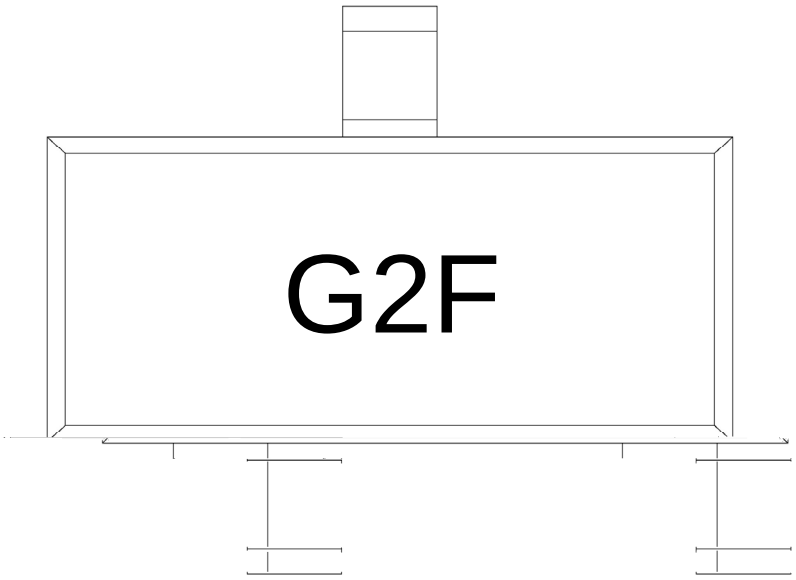
/ Package Dimensions

SOT-23

单位：mm



/ Marking Instructions



G

2F

Note:

G	HF Product Code
2F	Product Type Code